FDN86246

150 V, 1.6 A, 261 mΩ

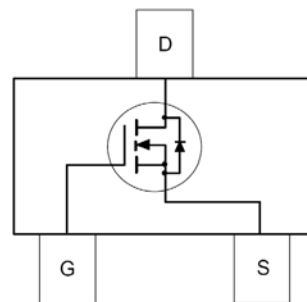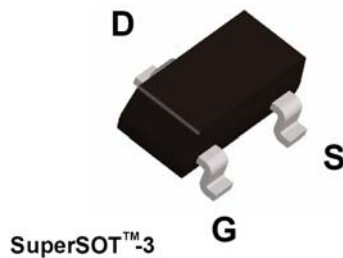### Features

- Max $r_{DS(on)}$ = 261 mΩ at V_{GS} = 10 V, I_D = 1.6 A

- Max $r_{DS(on)}$ = 359 mΩ at V_{GS} = 6 V, I_D = 1.4 A

- High performance trench technology for extremely low $r_{DS(on)}$

- High power and current handling capability in a widely used surface mount package

- Fast switching speed

- 100% UIL tested

- RoHS Compliant

Application

- PD Switch

SuperSOT™-3

MOSFET Maximum Ratings T_A = 25 °C unless otherwise noted

Symbol	Parameter		Ratings	Units
V_{DS}	Drain to Source Voltage		150	V
V_{GS}	Gate to Source Voltage		±20	V
I_D	-Continuous	(Note 1a)	1.6	A
	-Pulsed		6	
E_{AS}	Single Pulse Avalanche Energy	(Note 3)	13	mJ
P_D	Power Dissipation	(Note 1a)	1.5	W
	Power Dissipation	(Note 1b)	0.6	
T_J, T_{STG}	Operating and Storage Junction Temperature Range		-55 to +150	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	(Note 1)	75	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	80	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
246	FDN86246	SSOT-3	7 ''	8 mm	3000 units

FDN86246

Electrical Characteristics T_J = 25 °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250 μA, V_{GS} = 0 V	150			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25 °C		106		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 120 V, V_{GS} = 0 V			1	μA
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±20 V, V_{DS} = 0 V			±100	nA
On Characteristics (Note 2)						
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 250 μA	2	3.4	4	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25 °C		-9		mV/°C
$r_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10 V, I_D = 1.6 A		195	261	mΩ
		V_{GS} = 6 V, I_D = 1.4 A		242	359	
		V_{GS} = 10 V, I_D = 1.6 A, T_J = 125 °C		359	481	
g_{FS}	Forward Transconductance	V_{DS} = 10 V, I_D = 1.6 A		4		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 75 V, V_{GS} = 0 V, f = 1 MHz		168	225	pF
C_{oss}	Output Capacitance			21	30	pF
C_{rss}	Reverse Transfer Capacitance			1.6	5	pF
R_g	Gate Resistance			0.9		Ω
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 75 V, I_D = 1.6 A, V_{GS} = 10 V, R_{GEN} = 6 Ω		4.5	10	ns
t_r	Rise Time			1.1	10	ns
$t_{d(off)}$	Turn-Off Delay Time			8	16	ns
t_f	Fall Time			2.9	10	ns
Q_g	Total Gate Charge	V_{GS} = 0 V to 10 V		2.9	5	nC
Q_g	Total Gate Charge	V_{GS} = 0 V to 5 V, V_{DD} = 75 V, I_D = 1.6 A		1.6	3	nC
Q_{gs}	Gate to Source Gate Charge			0.9		nC
Q_{gd}	Gate to Drain "Miller" Charge			0.8		nC
Drain-Source Diode Characteristics						
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0 V, I_S = 1.6 A (Note 2)		0.83	1.3	V
t_{rr}	Reverse Recovery Time	I_F = 1.6 A, di/dt = 100 A/μs		44	70	ns
Q_{rr}	Reverse Recovery Charge			29	47	nC

Notes:
1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.

a) 80 °C/W when mounted on a 1 in^2 pad of 2 oz copper

b) 180 °C/W when mounted on a minimum pad.

2. Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0%.

3. Starting T_J = 25 °C; N-ch: L = 3 mH, I_{AS} = 3 A, V_{DD} = 150 V, V_{GS} = 10 V.